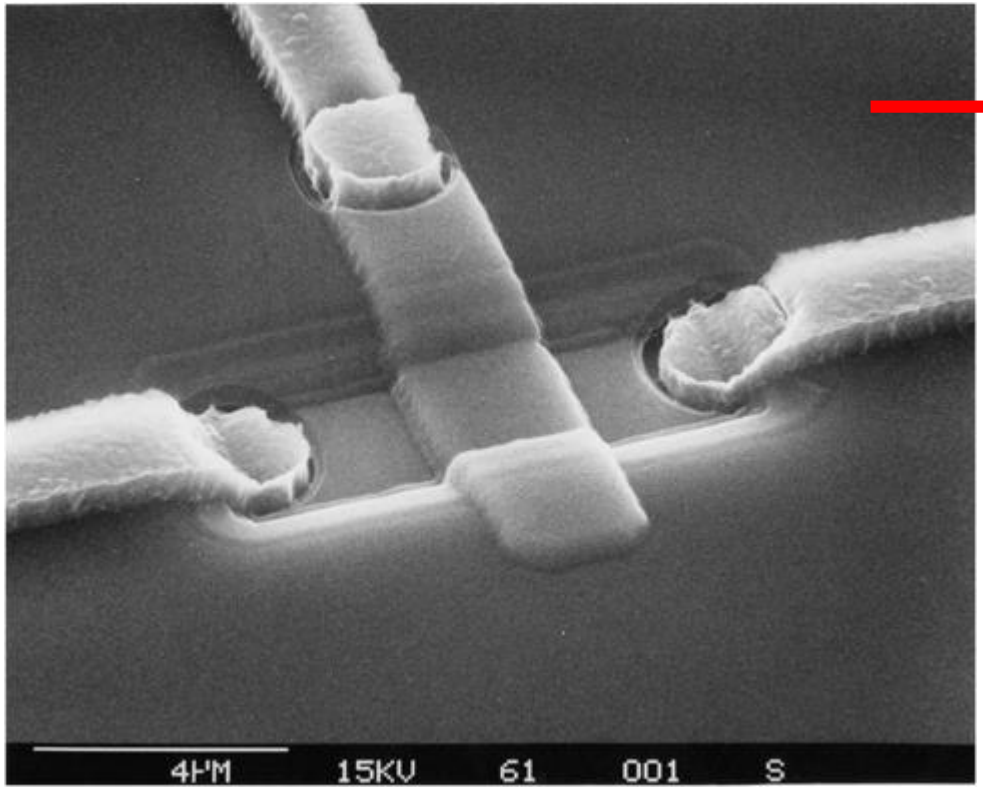
Silicon is to Physics what Carbon is to Life

Robert Klanner
Gerhard Lutz

Erik H.M. Heijne

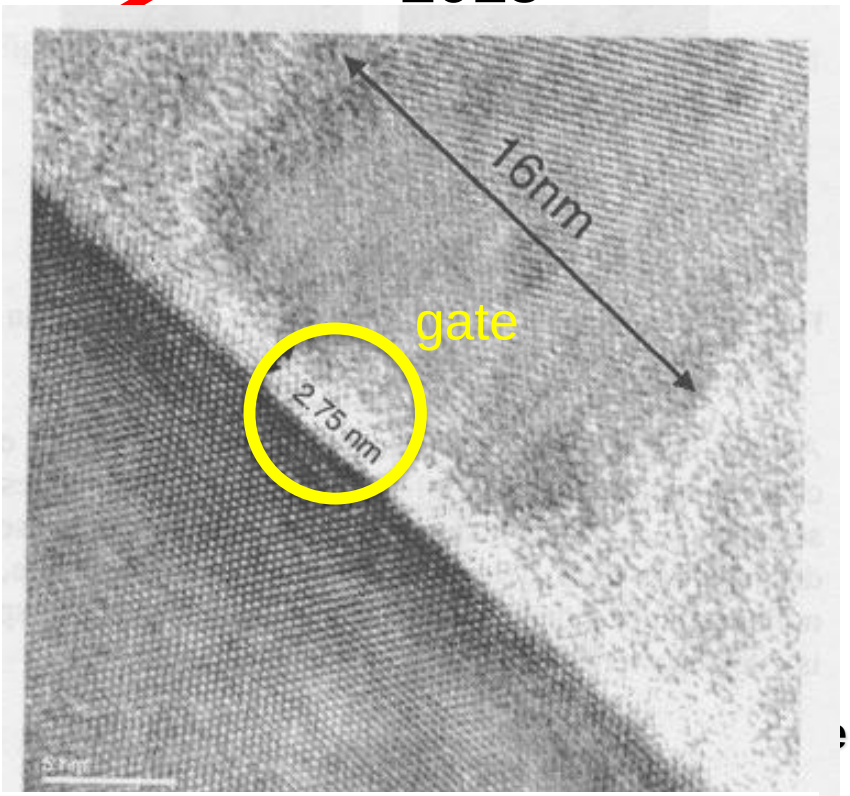
CERN EP Department Geneva
Inst. of Experimental and Applied Physics
of the Czech Technical University in Prague
National Institute Nikhef Amsterdam

Integrated electronics is key: silicon MOS transistor



continuous scaling/miniaturization

2015



2 μm TECHNOLOGY

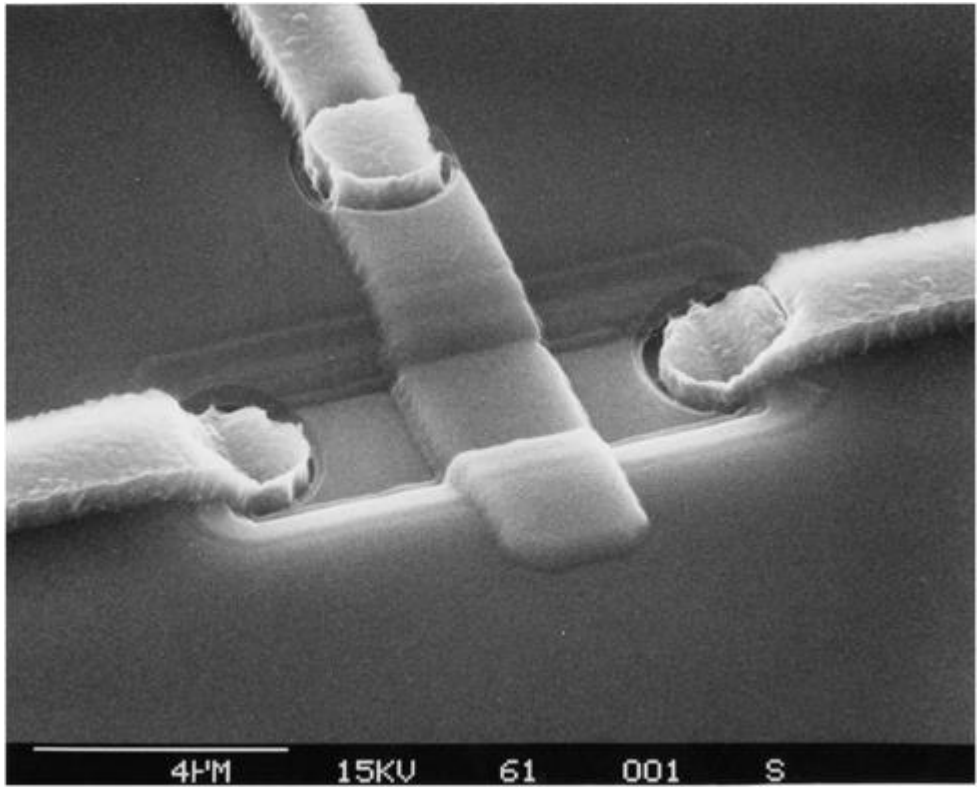
1985

HEP was 2 generations behind industry

gate length .016 μm

SiO_2 gate thickness 2.75 nm

Integrated electronics is key: silicon MOS transistor



continuous scaling/miniaturization

2015

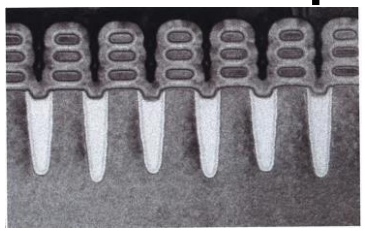
same scale

gate length .016 μm

SiO_2 gate thickness 2.75 nm

thin gate usually radhard

2017 development at IBM



gate-all-around source IBM

not same scale

2 μm TECHNOLOGY

1985

HEP was 2 generations behind industry

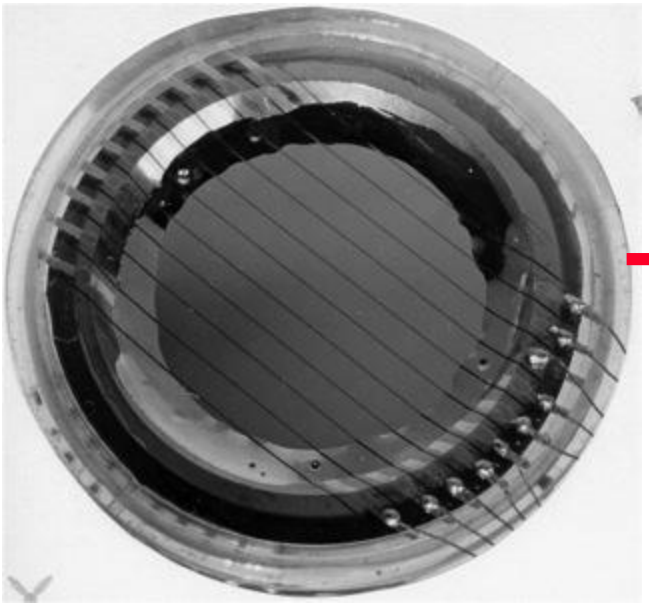
0.005 μm

2017

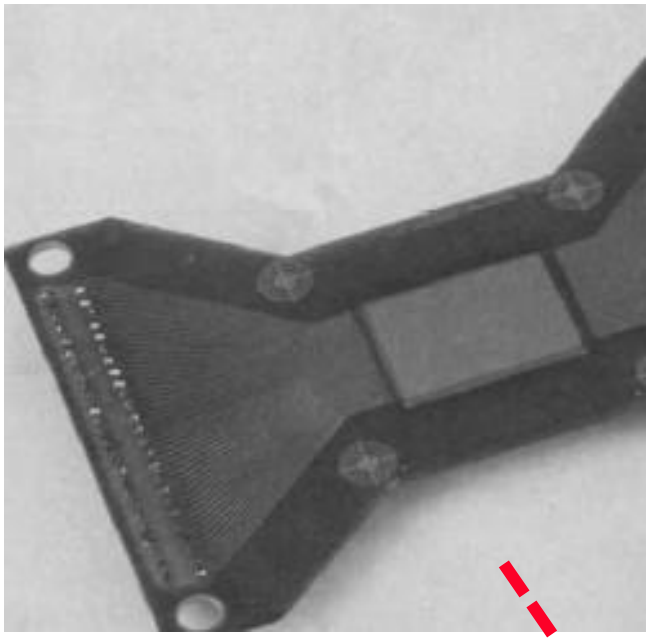
now HEP is 8 generations behind

Segmented silicon detectors

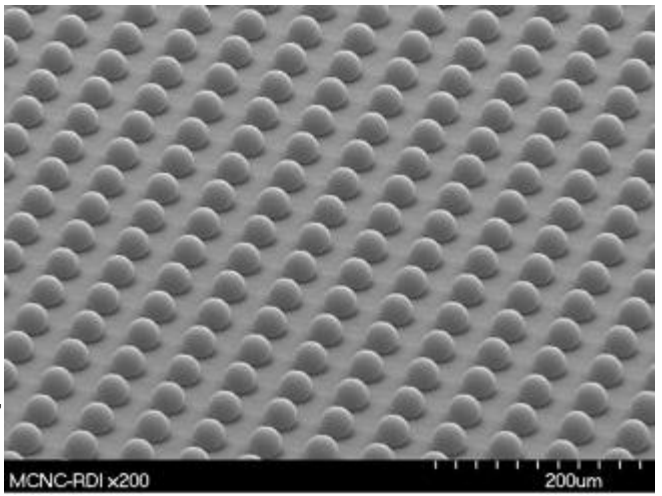
Thanks to Educators, Collaborators and Supporters



~1965
PHILIPS-Amsterdam
100 x 1370µm x 1370µm
Ammerlaan, van Dantzig, Visschers



1980 CERN / ENERTEC Strasbourg
100 x 4000µm x 200µm
Jarron, Burger, CSEM, Kemmer



1989-2000
Pixel detectors developed at CERN
smallest pixel side ~50µm
Campbell, Snoeys, LAA, IMEC, ETHZ, EPFL, RD19, Omega, Medipix

Physics experiments should begin to use recent industrial Si technology (<20nm) and achieve:

- lower power for same functions
- ps timing
- more on-chip memory
- multilayer information processing
- economy of scale
- ....
- higher rates, better data
- new physics?

Future experiments will rely on newest electronics need timely R&D efforts, expertise and resources worldwide collaboration & tens of millions to do it right

Thank You